imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

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COMPLIANCE

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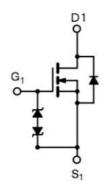
Pin Definition:

- 1. Source
- 2. Gate 3. Drain

PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (Ω)	I _D (mA)
60	5 @ V _{GS} = 10V	100
	5.5 @ V _{GS} = 5V	100

Block Diagram



N-Channel MOSFET

Low On-Resistance

Features

- ESD Protection
- High Speed Switching
- Low Voltage Drive

Ordering Information

Part No.	Package	Packing
TSM2N7000KCT B0G	TO-92	1Kpcs / Bulk
TSM2N7000KCT A3G	TO-92	2Kpcs / Ammo

Note: "G" denotes for Halogen Free

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V_{GS}	±20	V	
Drain Current	Continuous @ T _A =25ºC	I _D	300		
	Pulsed	I _{DM}	700	mA	
Drain Reverse Current	Continuous @ T _A =25ºC	I _{DR}	300	mA	
	Pulsed	I _{DMR}	700		
Maximum Power Dissipation		P _D	400	mW	
Operating Junction Temperature		Τ _J	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	TL	10	S
Junction to Ambient Thermal Resistance (PCB mounted)	RƏ _{JA}	357	°C/W

Notes:

a. Pulse width limited by the Maximum junction temperature

b. Surface Mounted on FR4 Board, t \leq 5 sec.



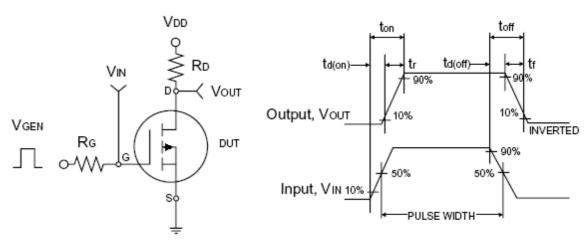
Electrical Specifications (Ta = 25°C, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 10\mu A$	BV _{DSS}	60			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V _{GS(TH)}	1.0		2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±10	uA
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I _{DSS}			1.0	uA
	$V_{GS} = 10V, I_{D} = 100mA$			3	5	Ω
Drain-Source On-State Resistance	$V_{GS} = 5V, I_{D} = 100mA$	R _{DS(ON)}		3.6	5.5	
Forward Transconductance	$V_{DS} = 10V, I_{D} = 200mA$	g _{fs}	100			mS
Diode Forward Voltage	$I_{S} = 300 \text{mA}, V_{GS} = 0 \text{V}$	V _{SD}		0.9	1.2	V
Dynamic ^ь						
Total Gate Charge	$V_{DS} = 10V, I_D = 250mA,$ $V_{GS} = 4.5V$	Qg		0.4		nC
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C _{iss}		7.32		
Output Capacitance		C _{oss}		3.42		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		7.63		
Switching ^c		•				
Turn-On Delay Time	$V_{DD} = 30V, R_{G} = 10\Omega$	t _{d(on)}		25		
Turn-Off Delay Time	$I_{\rm D} = 100 {\rm mA}, V_{\rm GEN} = 10 {\rm V},$	t _{d(off)}		35		nS

Notes:

a. pulse test: PW ≤300µS, duty cycle ≤2% b. For DESIGN AID ONLY, not subject to production testing.

b. Switching time is essentially independent of operating temperature.

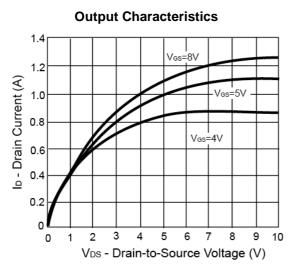


Switching Test Circuit

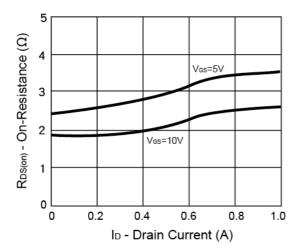
Switchin Waveforms



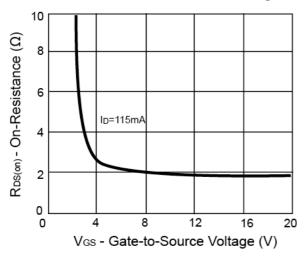
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

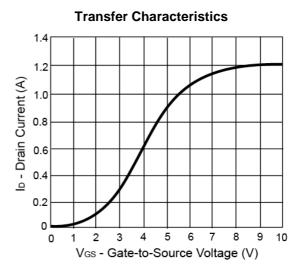


On-Resistance vs. Drain Current

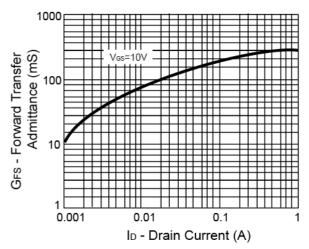


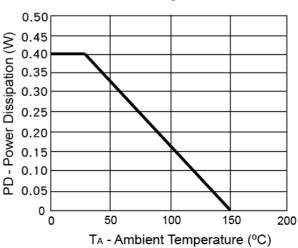
On-Resistance vs. Gate-Source Voltage





Forward Transfer Admittance vs. Drain Current

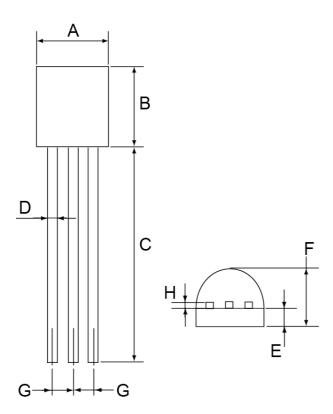




Power Derating Curve

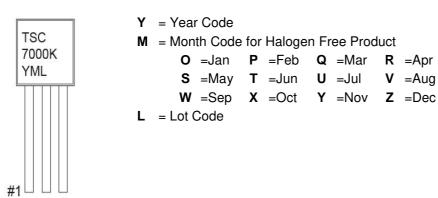


TO-92 Mechanical Drawing



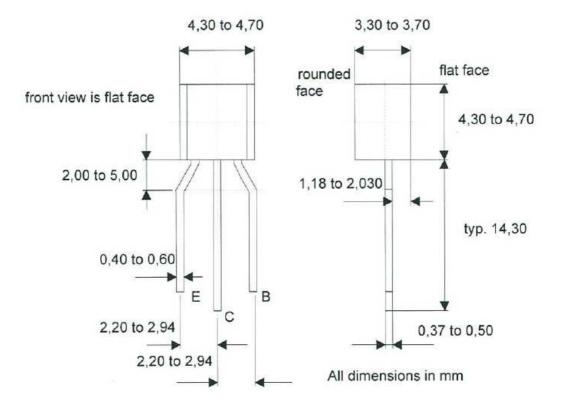
TO-92 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
А	4.30	4.70	0.169	0.185	
В	4.30	4.70	0.169	0.185	
С	13.53 (typ)		0.532 (typ)		
D	0.39	0.49	0.015	0.019	
Е	1.18	1.28	0.046	0.050	
F	3.30	3.70	0.130	0.146	
G	1.27	1.31	0.050	0.051	
Н	0.33	0.43	0.013	0.017	

Marking Diagram





TO-92 Ammo Pack Mechanical Drawing



TAIWAN

Pb

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COMPLIANCE



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